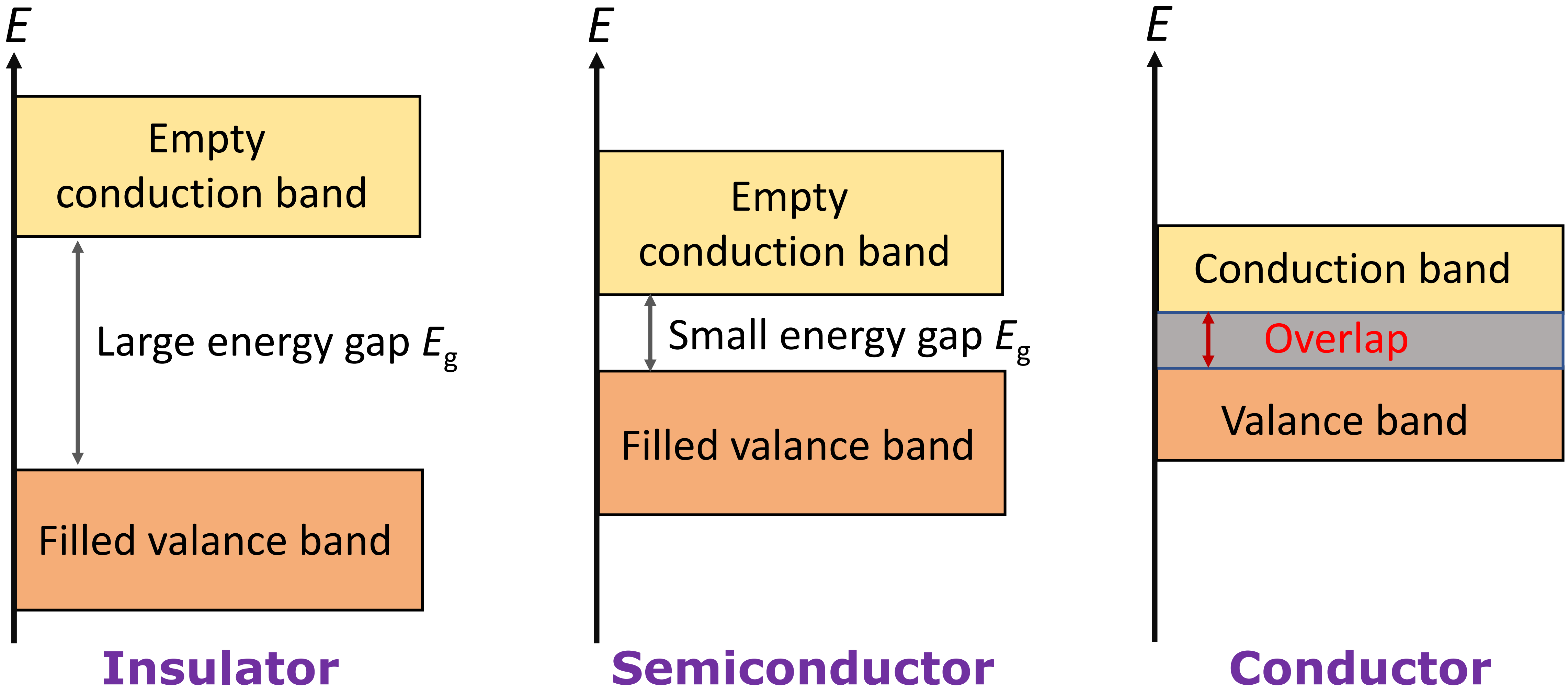
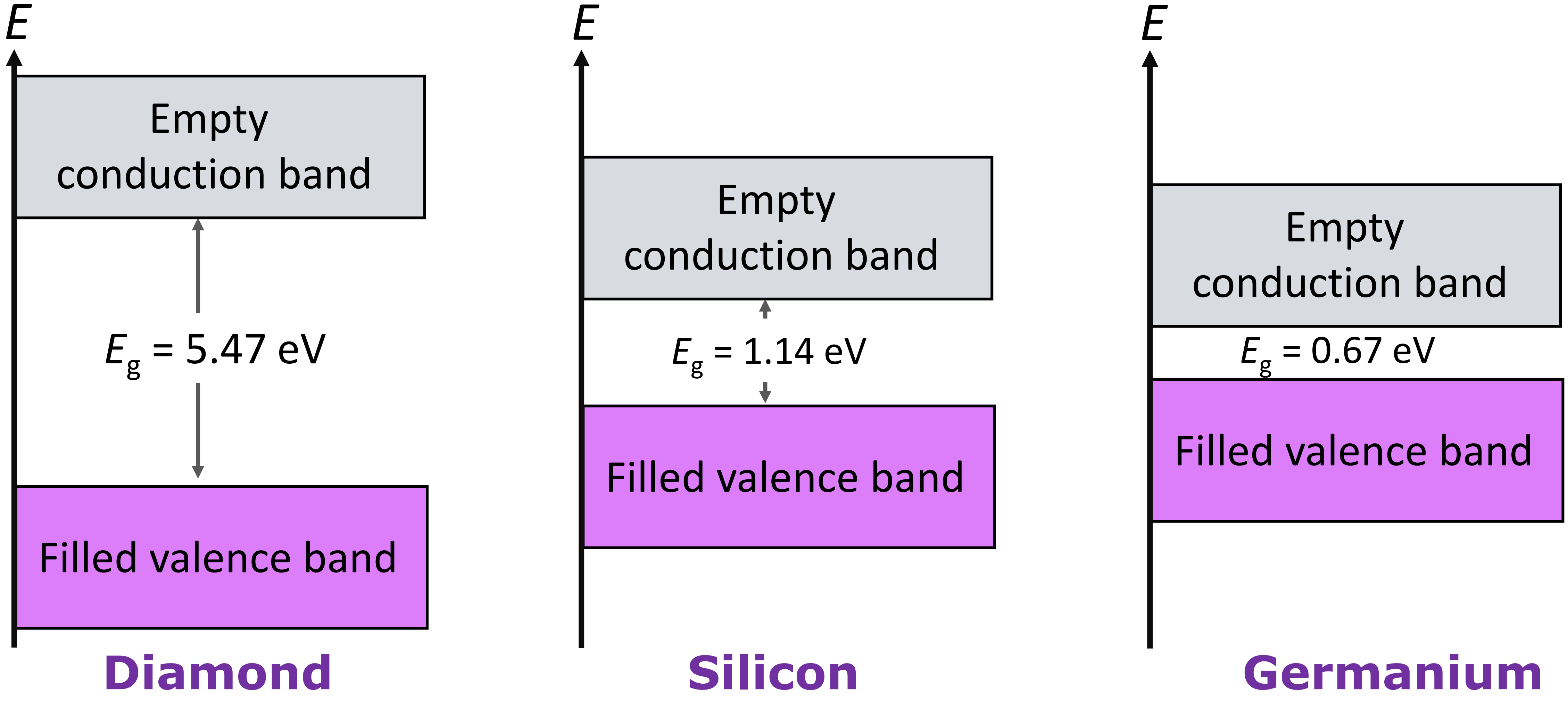
Intrinsic and extrinsic semiconductors

Dr Mohammad Abdur Rashid

Energy Bands for Solids



Semiconductor



Semiconductor

Semiconductor	InSb	GaAs	GaP	ZnSe
E_g (eV)	0.18	1.42	2.25	2.7

$$E = k_B T$$

$1 \text{ eV} = 1.6 \times 10^{-19}$ J

300 K ≈ 0.026 eV

Periodic Table of the Elements

1 IA 1A	2 IIA 2A	3 IIIB 3B	4 IVB 4B	5 VB 5B	6 VIB 6B	7 VIIB 7B	8	9 VIII 8	10	11 IB 1B	12 IIB 2B	13 IIIA 3A	14 IVA 4A	15 VA 5A	16 VIA 6A	17 VIIA 7A	18 VIIIA 8A
1 H Hydrogen 1.008																	2 He Helium 4.003
3 Li Lithium 6.941	4 Be Beryllium 9.012											5 B Boron 10.811	6 C Carbon 12.011	7 N Nitrogen 14.007	8 O Oxygen 15.999	9 F Fluorine 18.998	10 Ne Neon 20.180
11 Na Sodium 22.99	12 Mg Magnesium 24.305											13 Al Aluminum 26.982	14 Si Silicon 28.086	15 P Phosphorus 30.974	16 S Sulfur 32.066	17 Cl Chlorine 35.453	18 Ar Argon 39.948
19 K Potassium 39.098	20 Ca Calcium 40.078	21 Sc Scandium 44.956	22 Ti Titanium 47.867	23 V Vanadium 50.942	24 Cr Chromium 51.996	25 Mn Manganese 54.938	26 Fe Iron 55.845	27 Co Cobalt 58.933	28 Ni Nickel 58.693	29 Cu Copper 63.546	30 Zn Zinc 65.38	31 Ga Gallium 69.723	32 Ge Germanium 72.631	33 As Arsenic 74.922	34 Se Selenium 78.971	35 Br Bromine 79.904	36 Kr Krypton 83.789
37 Rb Rubidium 85.468	38 Sr Strontium 87.62	39 Y Yttrium 88.906	40 Zr Zirconium 91.224	41 Nb Niobium 92.906	42 Mo Molybdenum 95.95	43 Tc Technetium 98.907	44 Ru Ruthenium 101.07	45 Rh Rhodium 102.906	46 Pd Palladium 106.42	47 Ag Silver 107.868	48 Cd Cadmium 112.414	49 In Indium 114.818	50 Sn Tin 118.711	51 Sb Antimony 121.760	52 Te Tellurium 127.6	53 I Iodine 126.904	54 Xe Xenon 131.294
55 Cs Cesium 132.905	56 Ba Barium 137.328	57-71	72 Hf Hafnium 178.49	73 Ta Tantalum 180.948	74 W Tungsten 183.84	75 Re Rhenium 186.207	76 Os Osmium 190.23	77 Ir Iridium 192.217	78 Pt Platinum 195.085	79 Au Gold 196.967	80 Hg Mercury 200.592	81 Tl Thallium 204.383	82 Pb Lead 207.2	83 Bi Bismuth 208.980	84 Po Polonium [208.982]	85 At Astatine 209.987	86 Rn Radon 222.018
87 Fr Francium 223.020	88 Ra Radium 226.025	89-103	104 Rf Rutherfordium [261]	105 Db Dubnium [262]	106 Sg Seaborgium [266]	107 Bh Bohrium [264]	108 Hs Hassium [269]	109 Mt Meitnerium [278]	110 Ds Darmstadtium [281]	111 Rg Roentgenium [280]	112 Cn Copernicium [285]	113 Nh Nihonium [286]	114 Fl Flerovium [289]	115 Mc Moscovium [286]	116 Lv Livermorium [293]	117 Ts Tennessine [294]	118 Og Oganesson [294]

Lanthanide Series	57 La Lanthanum 138.905	58 Ce Cerium 140.116	59 Pr Praseodymium 140.908	60 Nd Neodymium 144.243	61 Pm Promethium 144.913	62 Sm Samarium 150.36	63 Eu Europium 151.964	64 Gd Gadolinium 157.25	65 Tb Terbium 158.925	66 Dy Dysprosium 162.500	67 Ho Holmium 164.930	68 Er Erbium 167.259	69 Tm Thulium 168.934	70 Yb Ytterbium 173.055	71 Lu Lutetium 174.967
Actinide Series	89 Ac Actinium 227.028	90 Th Thorium 232.038	91 Pa Protactinium 231.036	92 U Uranium 238.029	93 Np Neptunium 237.048	94 Pu Plutonium 244.064	95 Am Americium 243.061	96 Cm Curium 247.070	97 Bk Berkelium 247.070	98 Cf Californium 251.080	99 Es Einsteinium [254]	100 Fm Fermium 257.095	101 Md Mendelevium 258.1	102 No Nobelium 259.101	103 Lr Lawrencium [262]

SCIENCE NOTES
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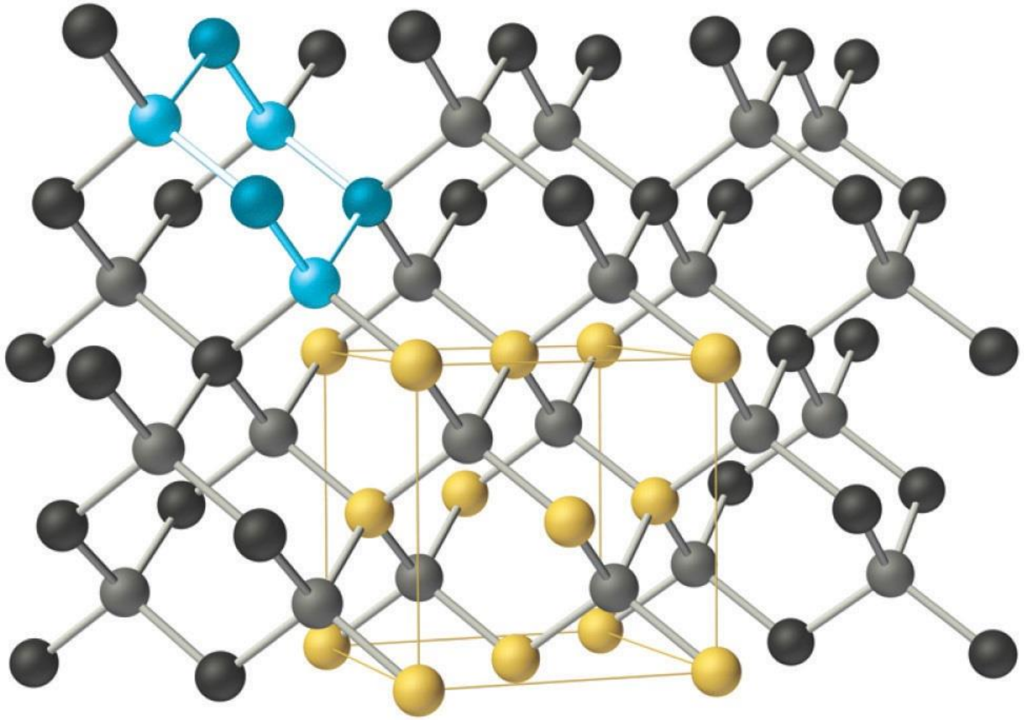
Alkali Metal	Alkaline Earth	Transition Metal	Basic Metal	Semimetal	Nonmetal	Halogen	Noble Gas	Lanthanide	Actinide

Silicon

Wikipedia
The Free Encyclopedia

Crystal Silicon



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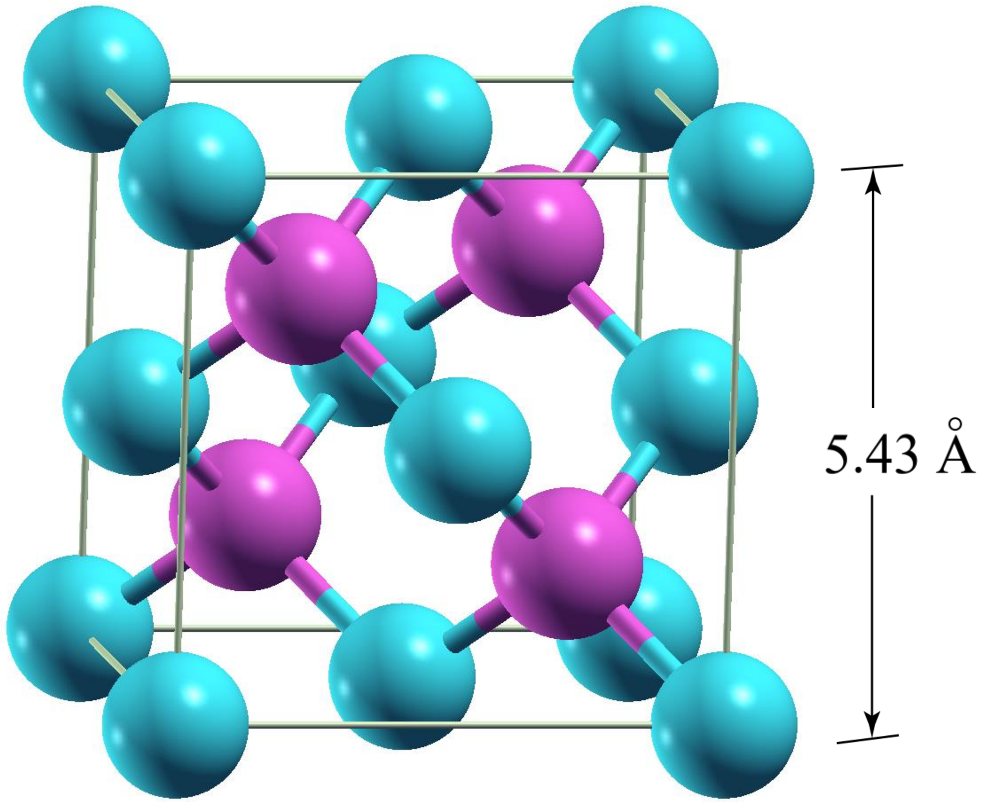
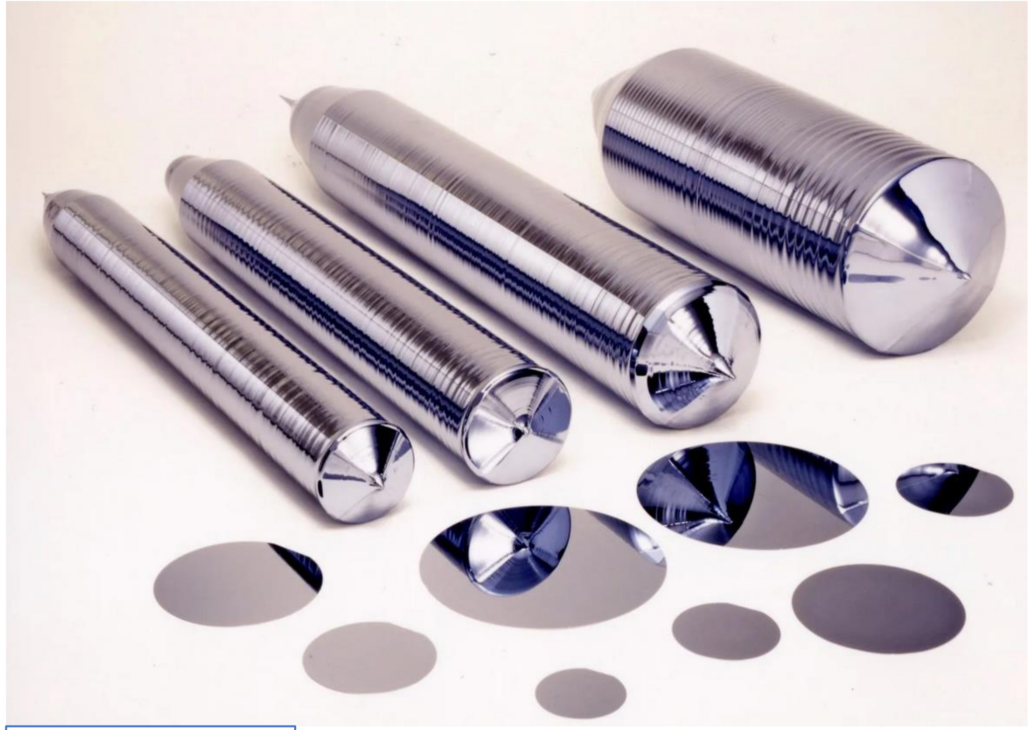


3sp tetrahedral bond

2.35Å

Silicon ingot

techdesignforums.com



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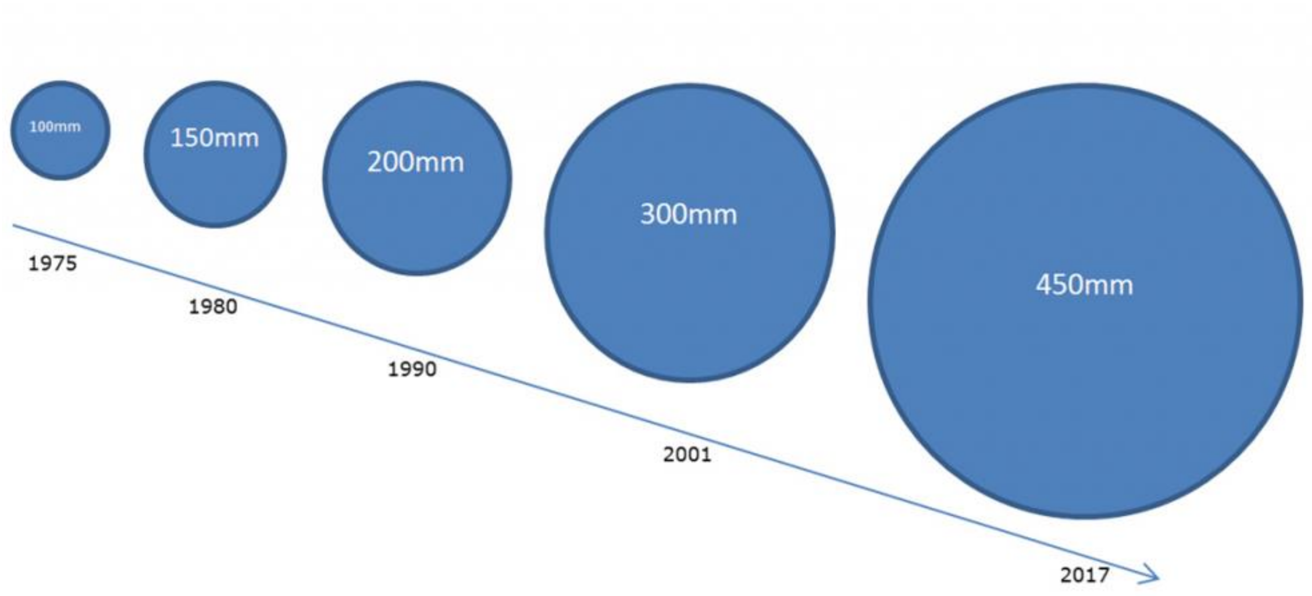
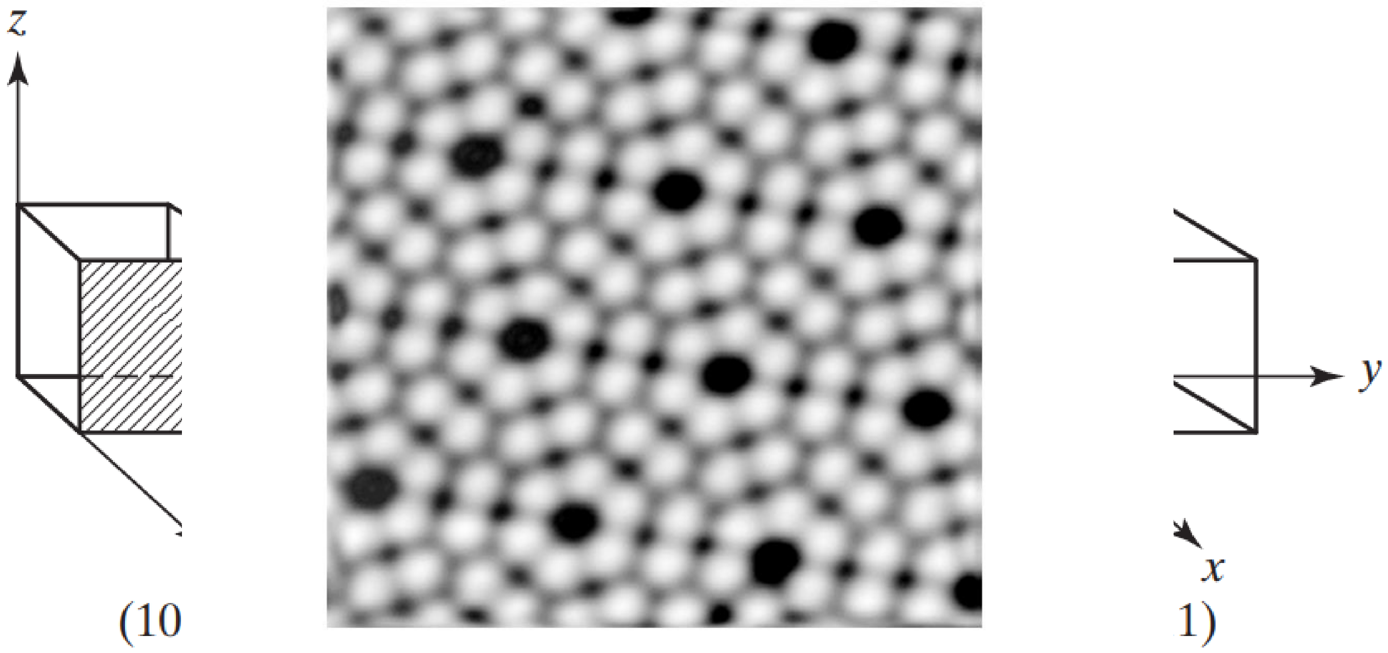
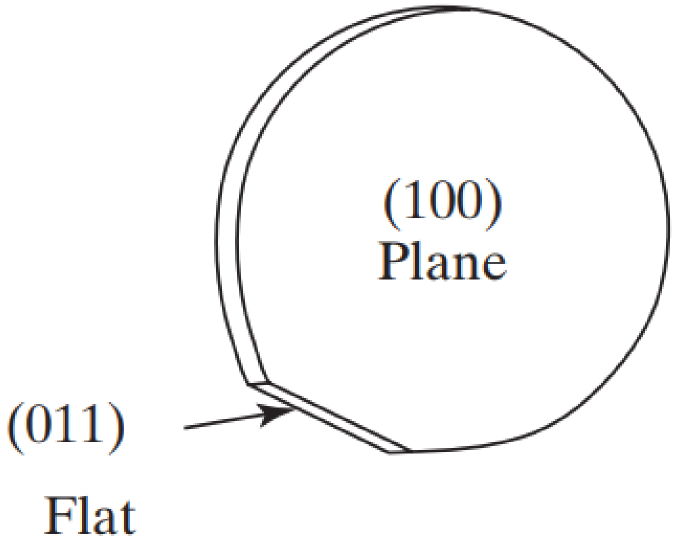


Silicon wafers





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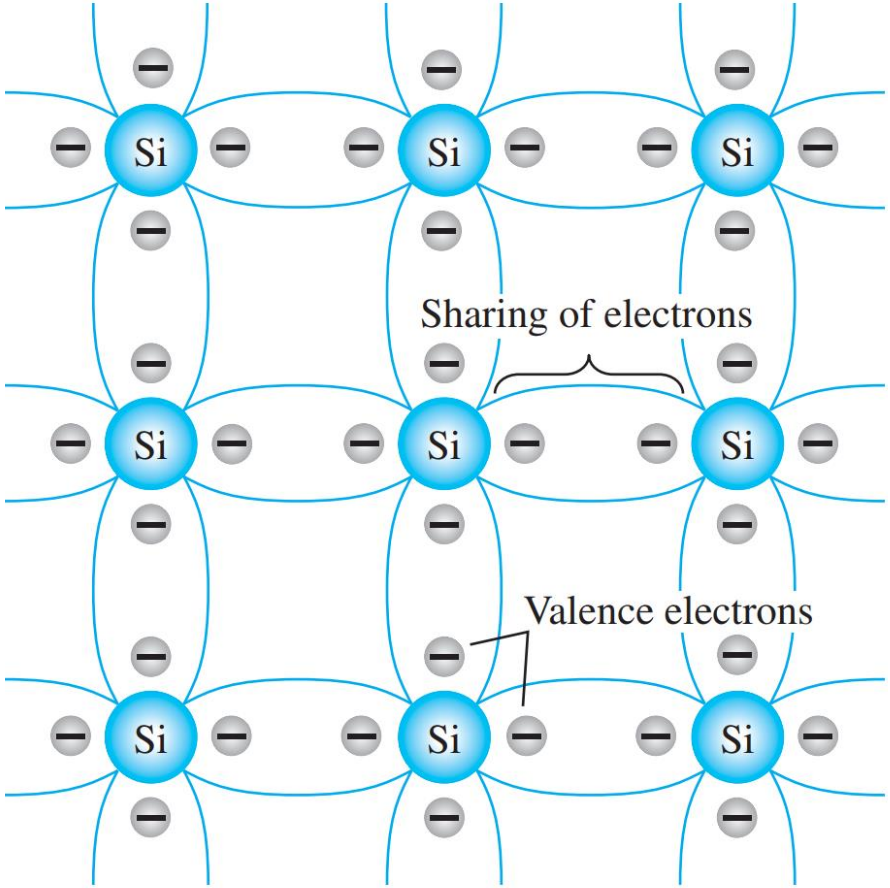
Covalent bonding of the silicon atom



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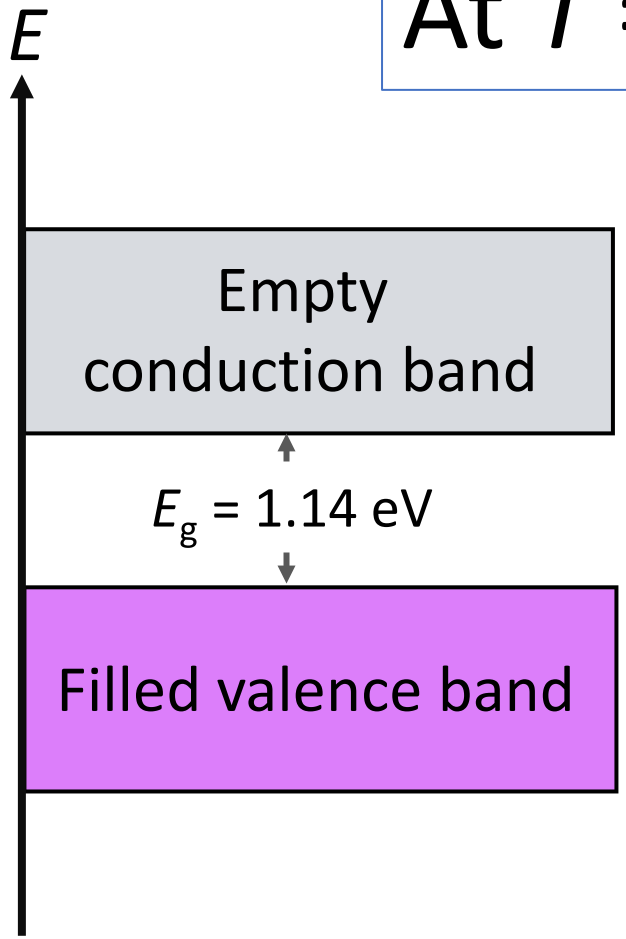
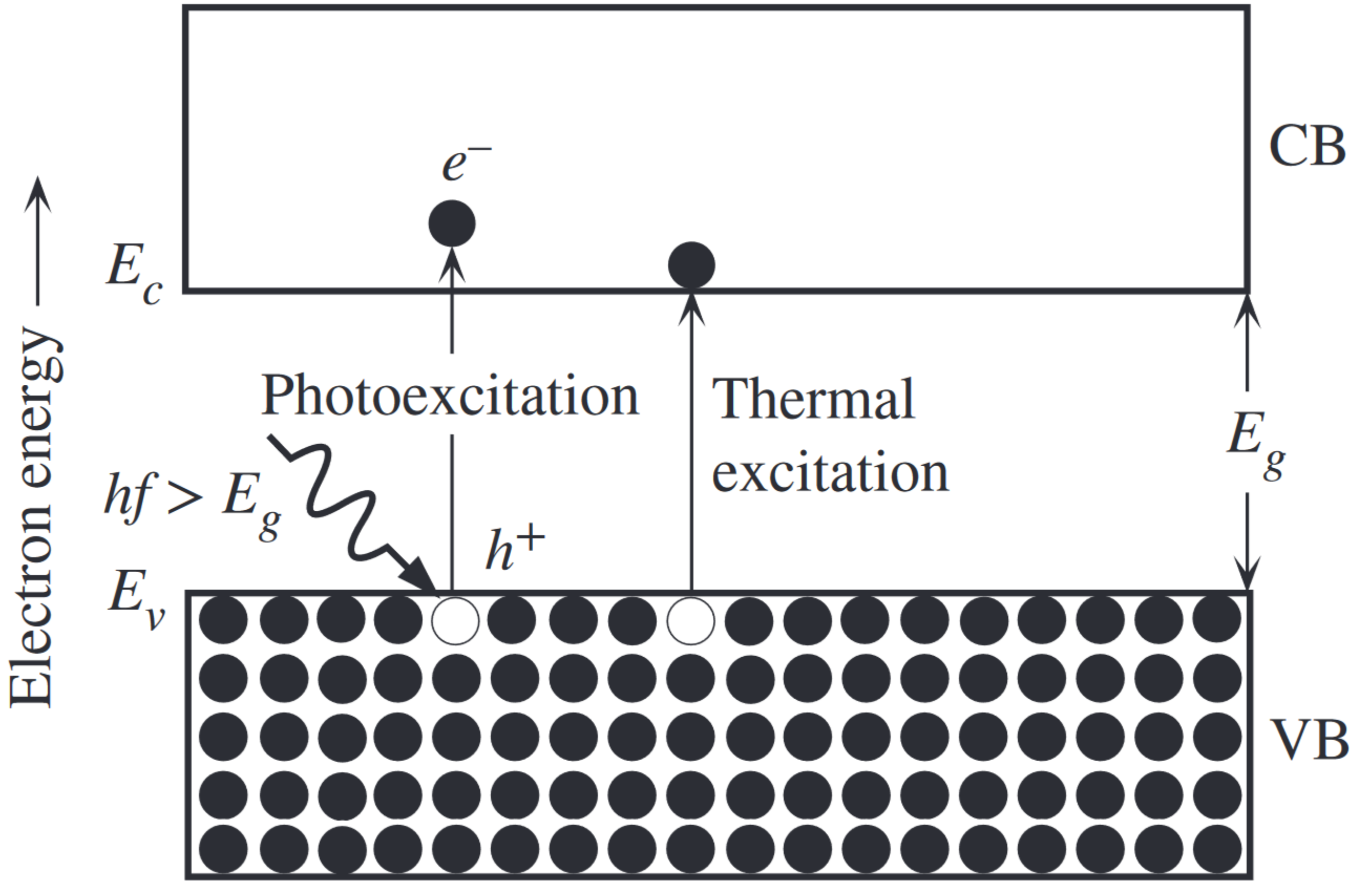
At T = 0 K



Excitation of electrons from VB to CB

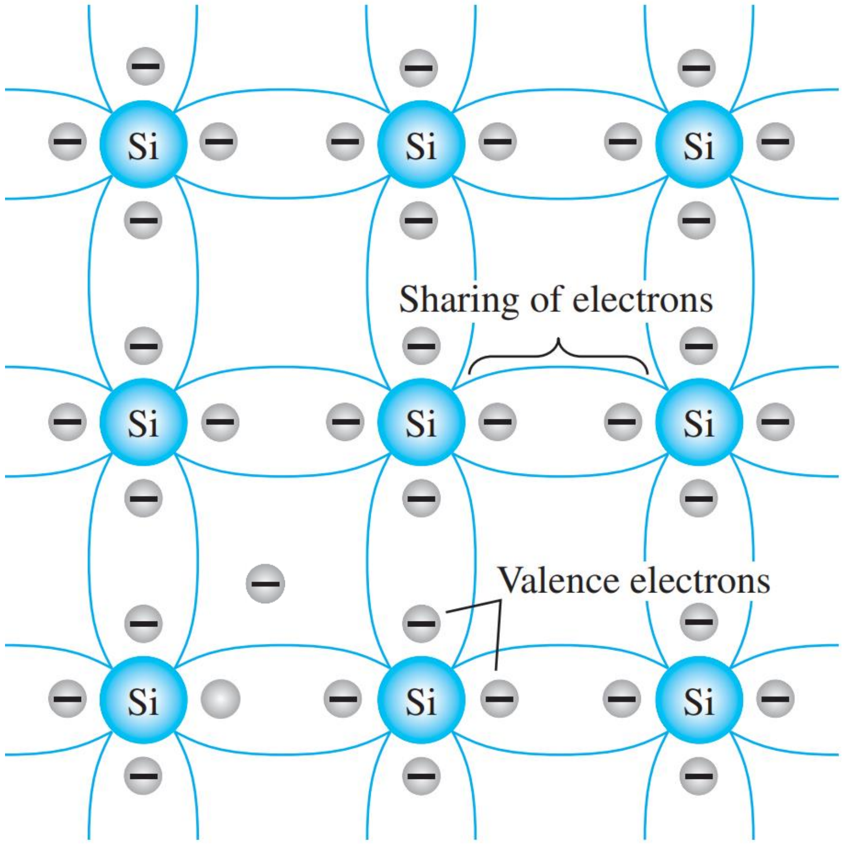
At room temperature



Electronic Materials & Devices – Kasap

Electron and Hole in intrinsic silicon

At room temperature there are approximately 1.5×10^{10} free carriers in 1 cm^3 of *intrinsic* silicon.



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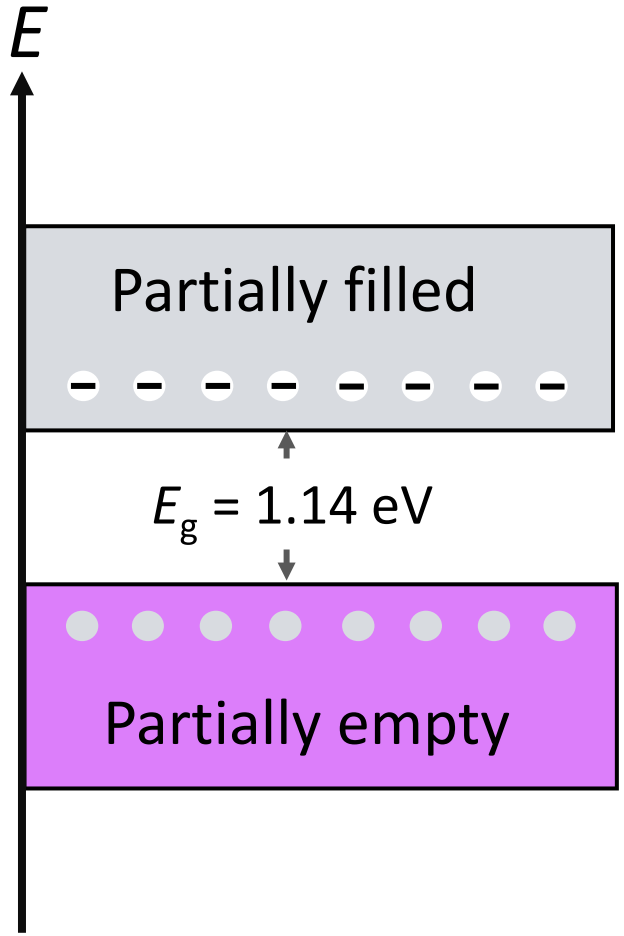

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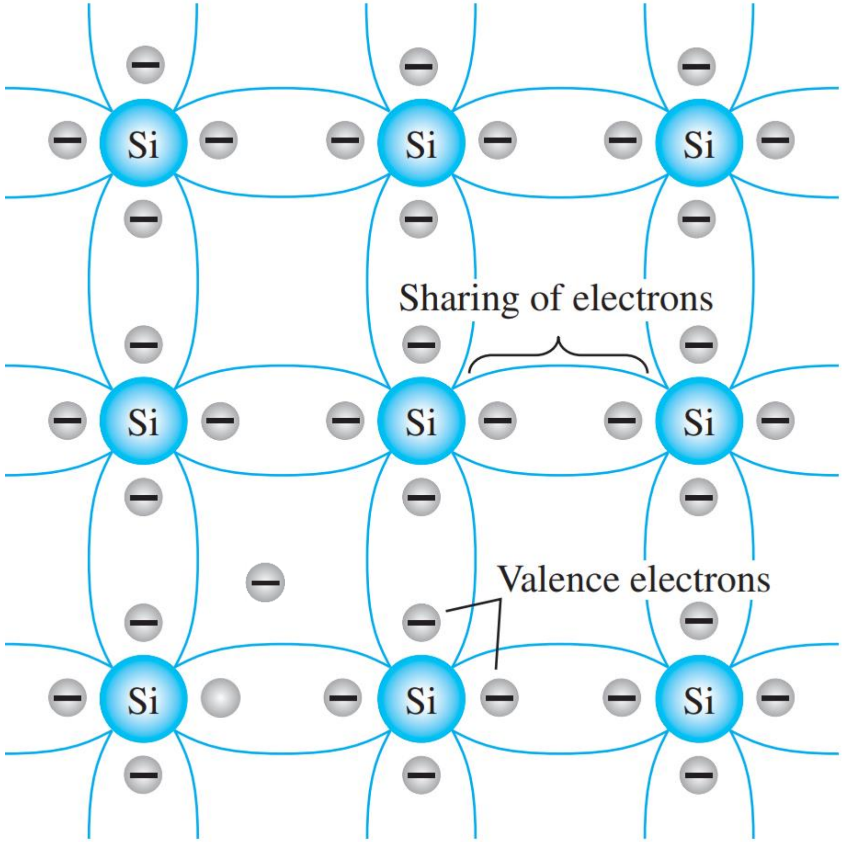

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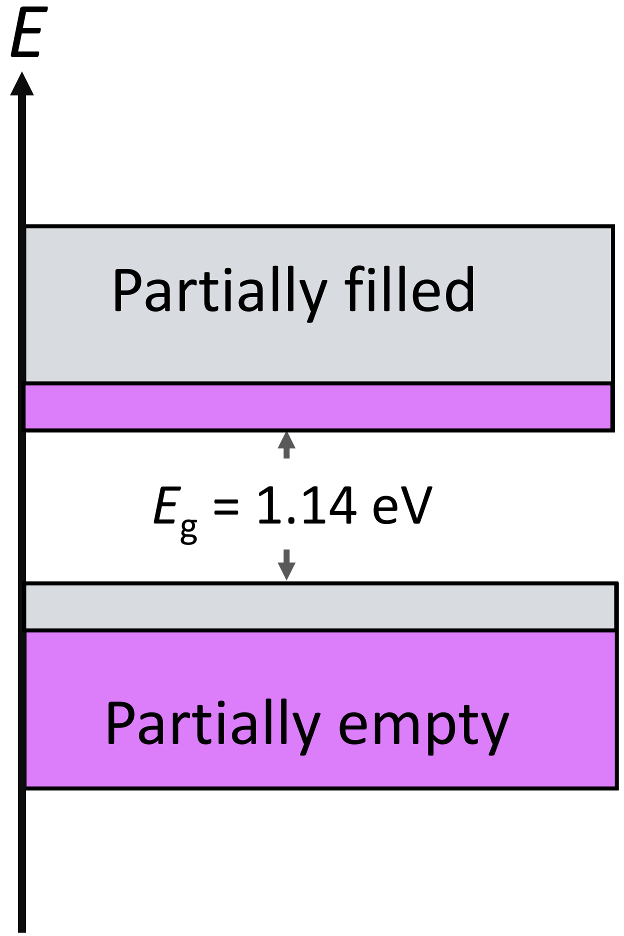
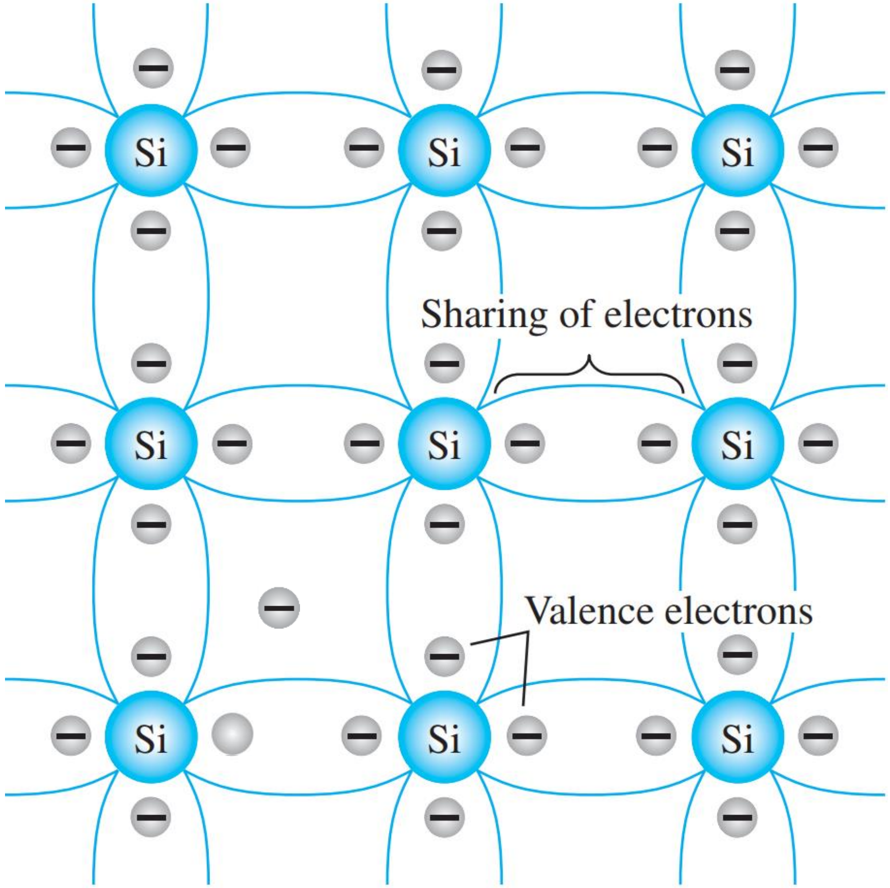


Electron and Hole in intrinsic silicon



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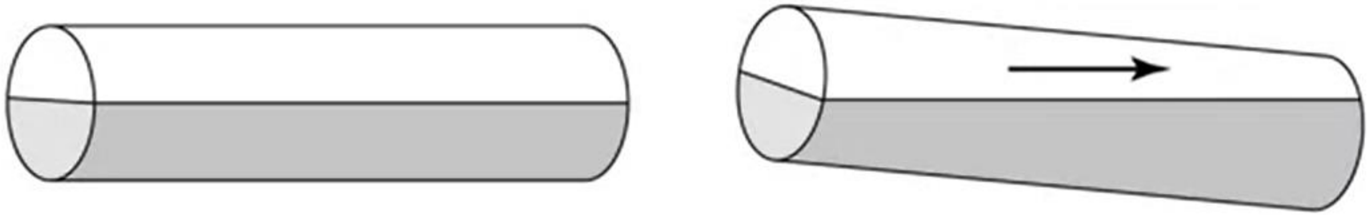
The external causes include effects such as light energy in the form of photons and thermal energy (heat) from the surrounding medium.

At room temperature there are approximately 1.5×10^{10} free carriers in 1 cm^3 of *intrinsic* silicon.

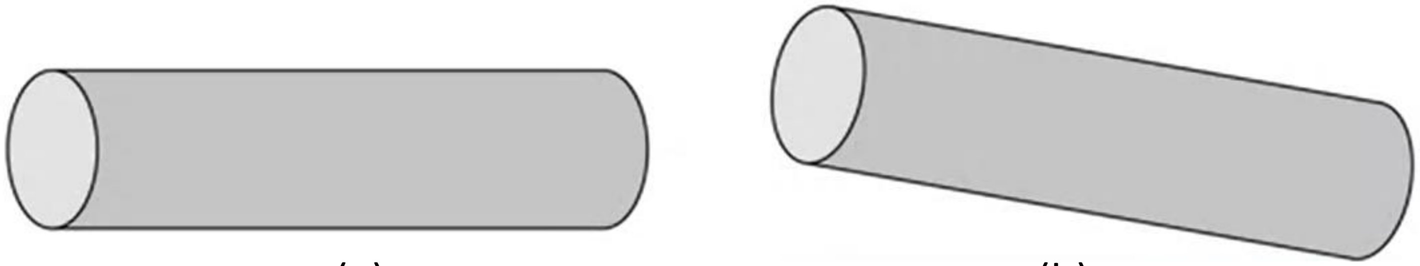
Fluid motion in a glass tube

- Half filled band
- Good electric conductors



(a) (b)

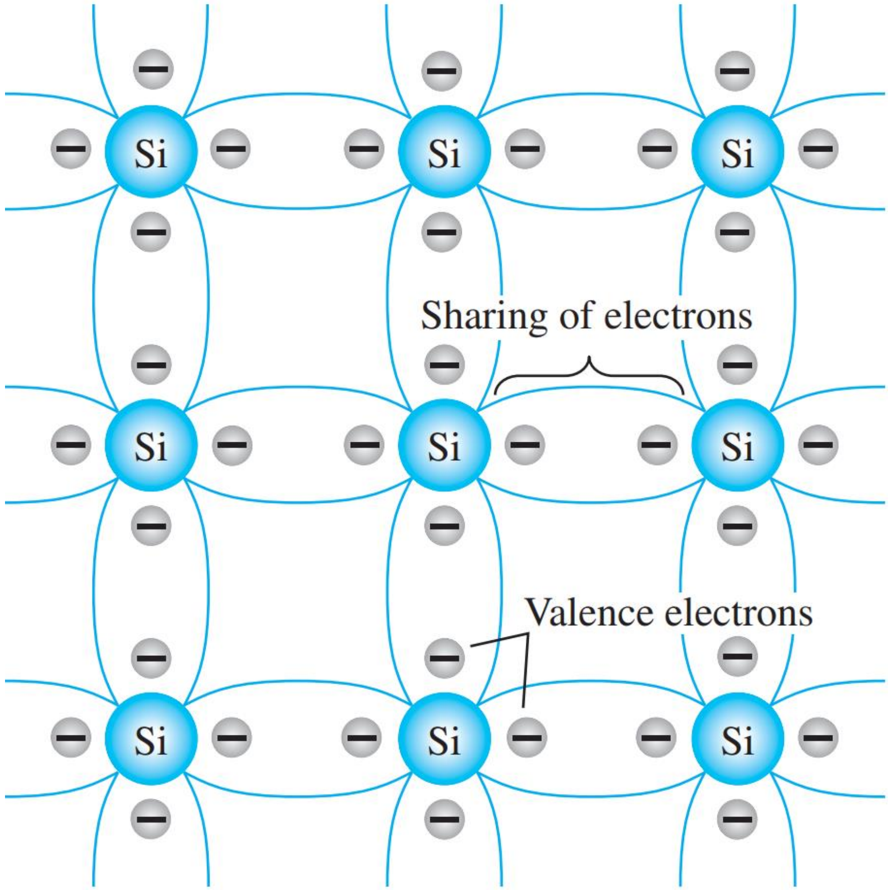
- Completely full or completely empty band
- Poor electric conductors



(a) (b)

Device Electronics for Integrated Circuits –Muller, Kamins, Chan

Extrinsic semiconductor



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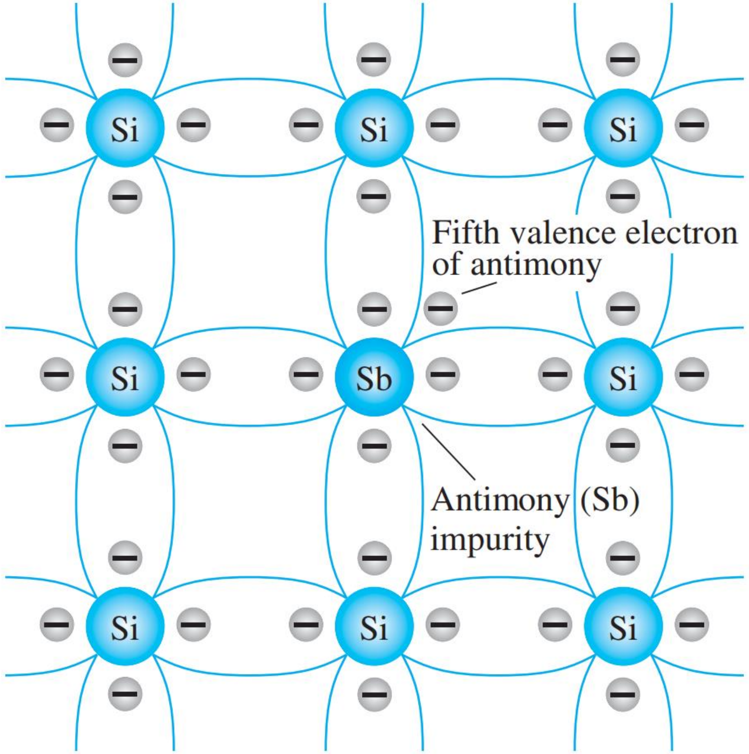
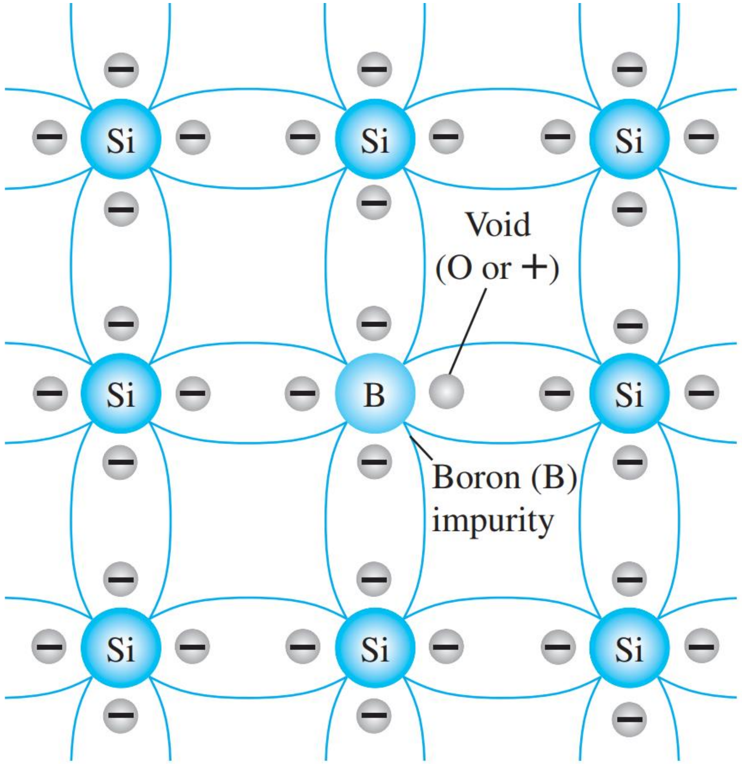
IIB	IIIA	IVA	VA	VIA
	5 B	6 C	7 N	8 O
	13 Al	14 Si	15 P	16 S
30 Zn	31 Ga	32 Ge	33 As	34 Se
48 Cd	49 In	50 Sn	51 Sb	52 Te

Extrinsic semiconductor

n-type material





p-type material

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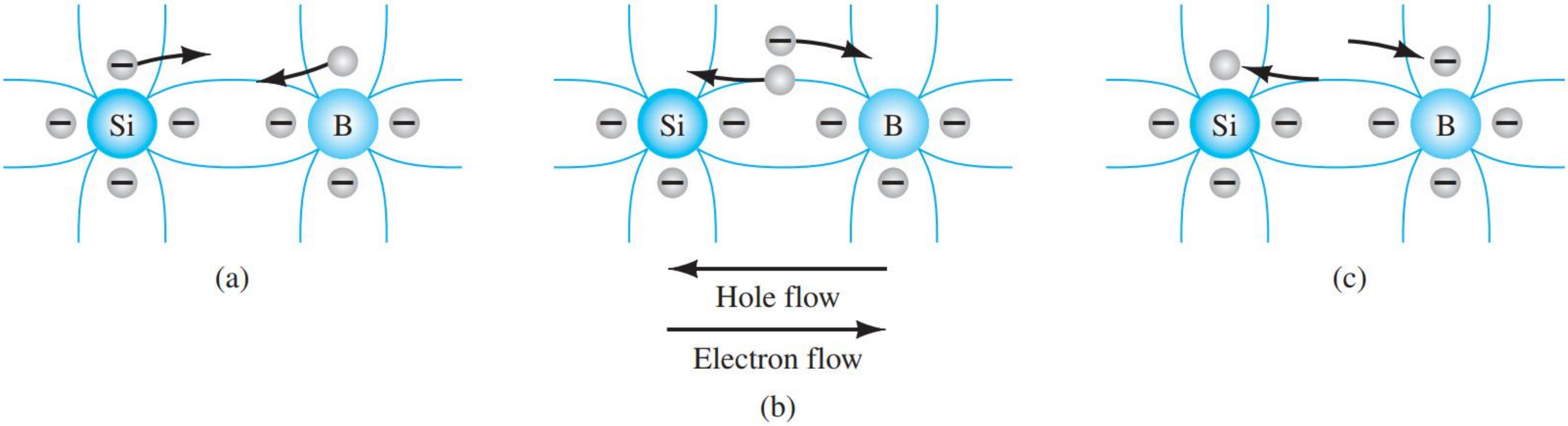
Electron versus Hole Flow



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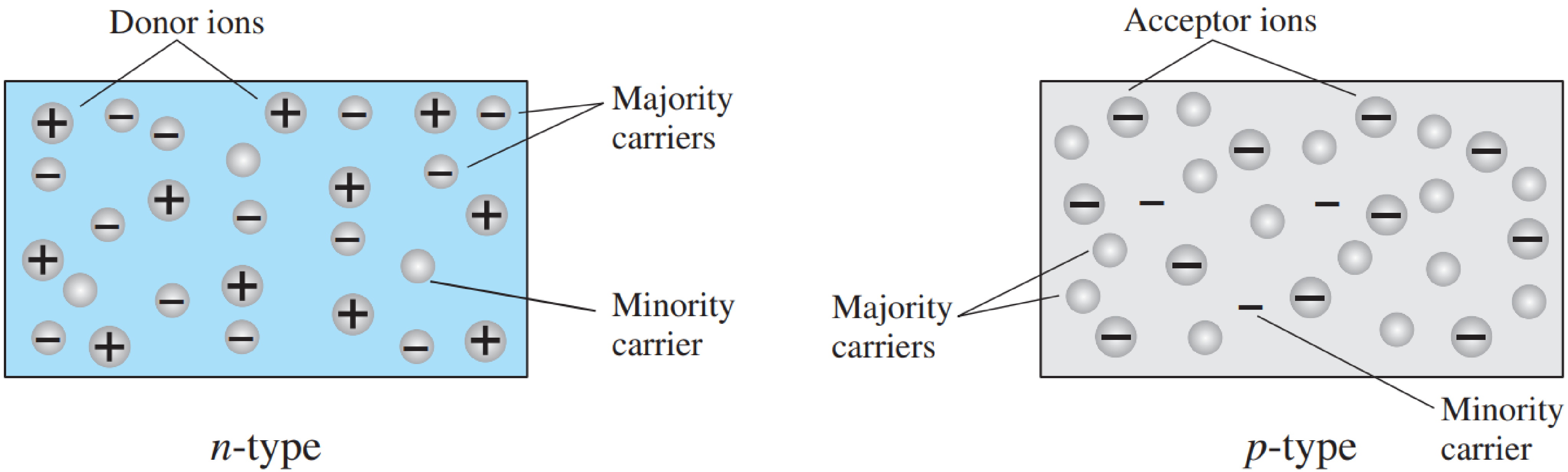
Majority and Minority Carriers



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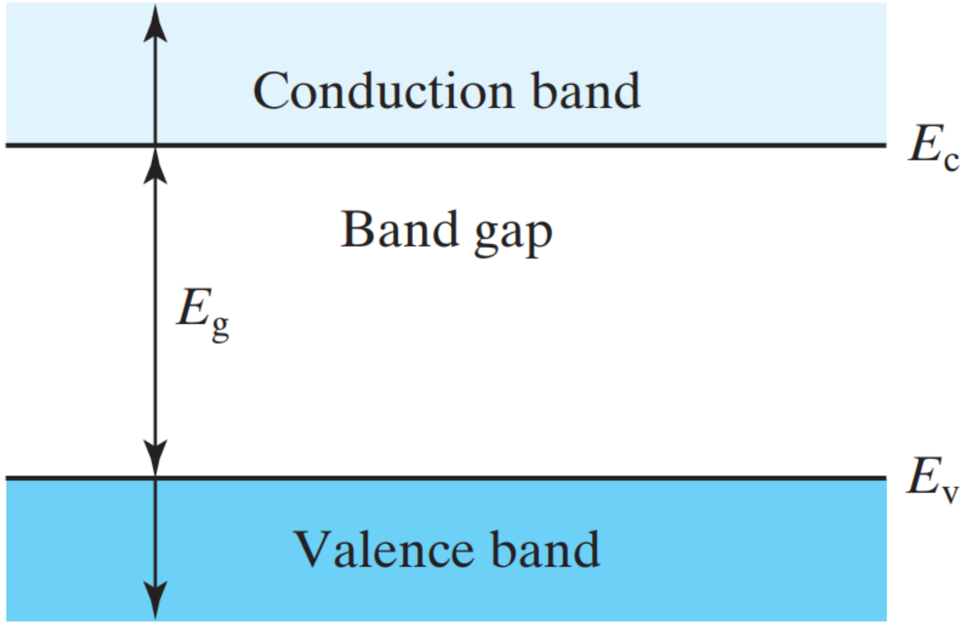
Energy band diagram



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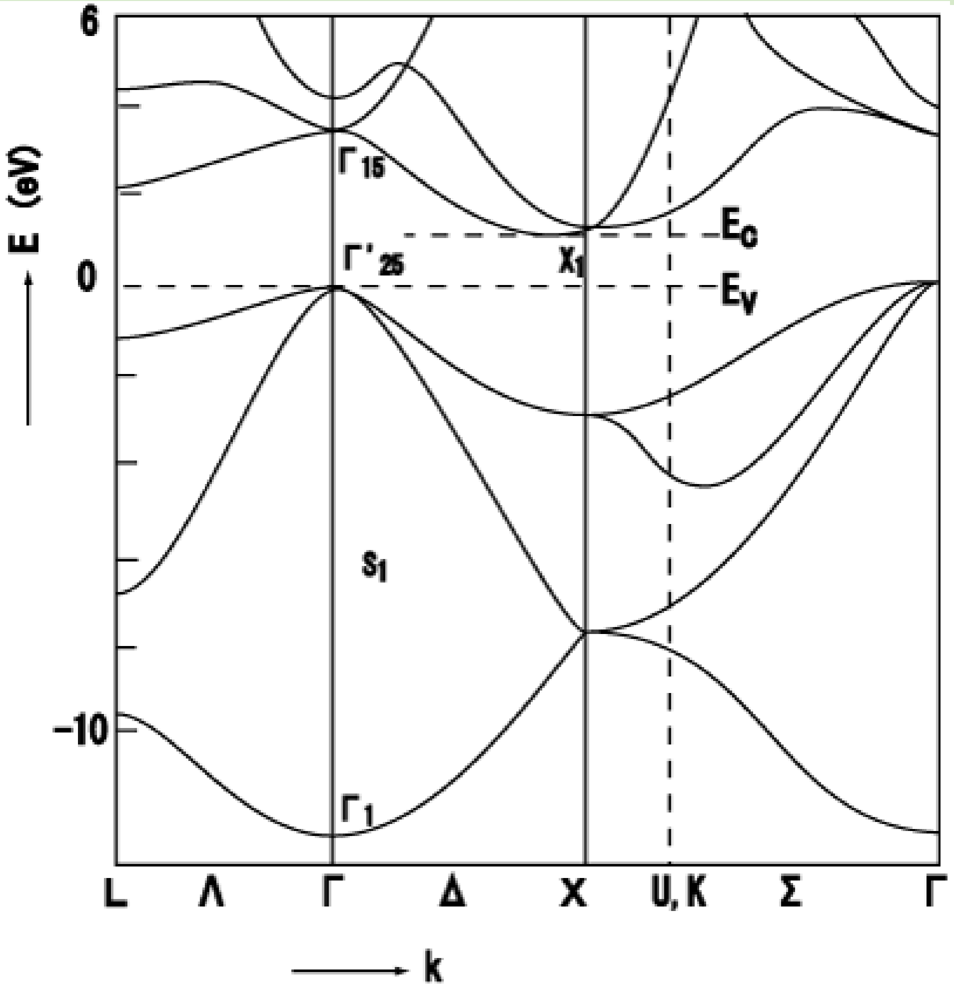
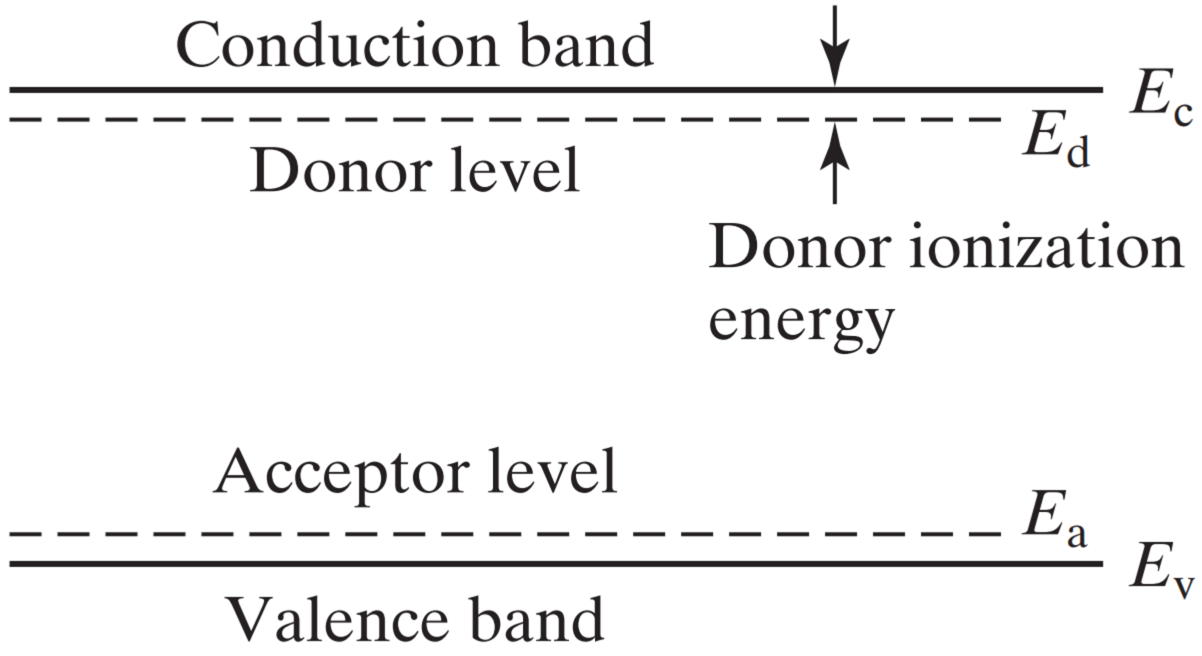


Chelikowsky et al., Phys. Rev. B 10, 5095 (1974)

Energy band diagram



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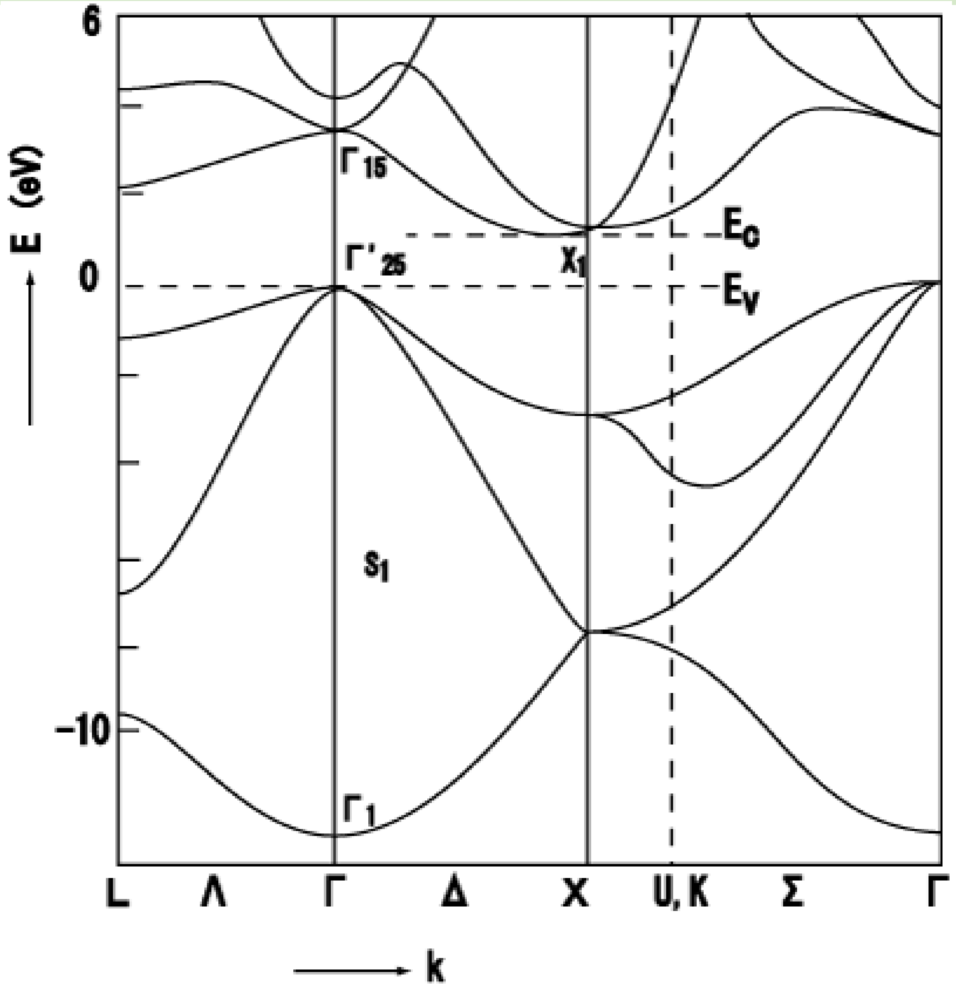
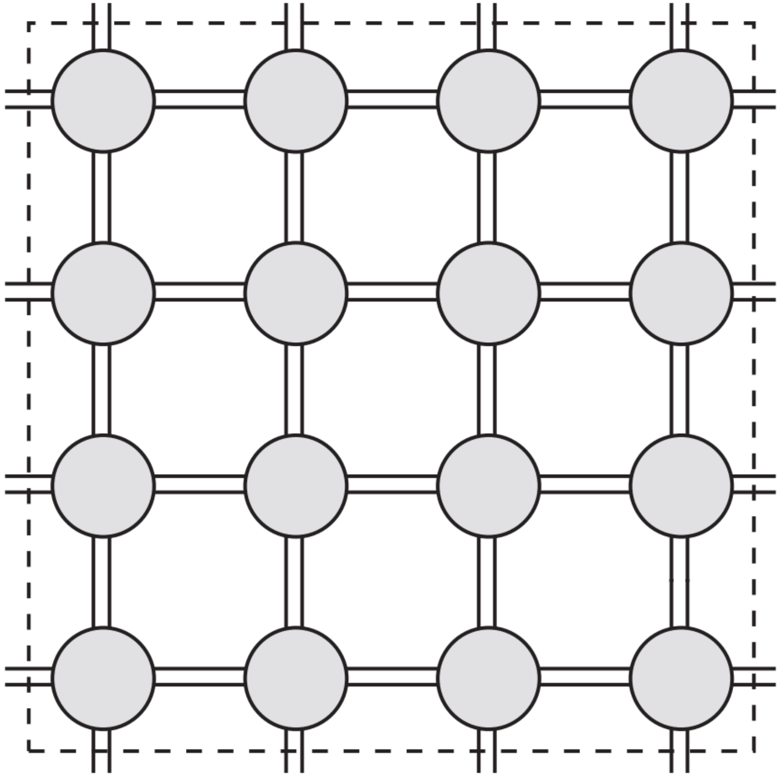


Chelikowsky et al., Phys. Rev. B 10, 5095 (1974)

Two-dimensional view of the Si crystal



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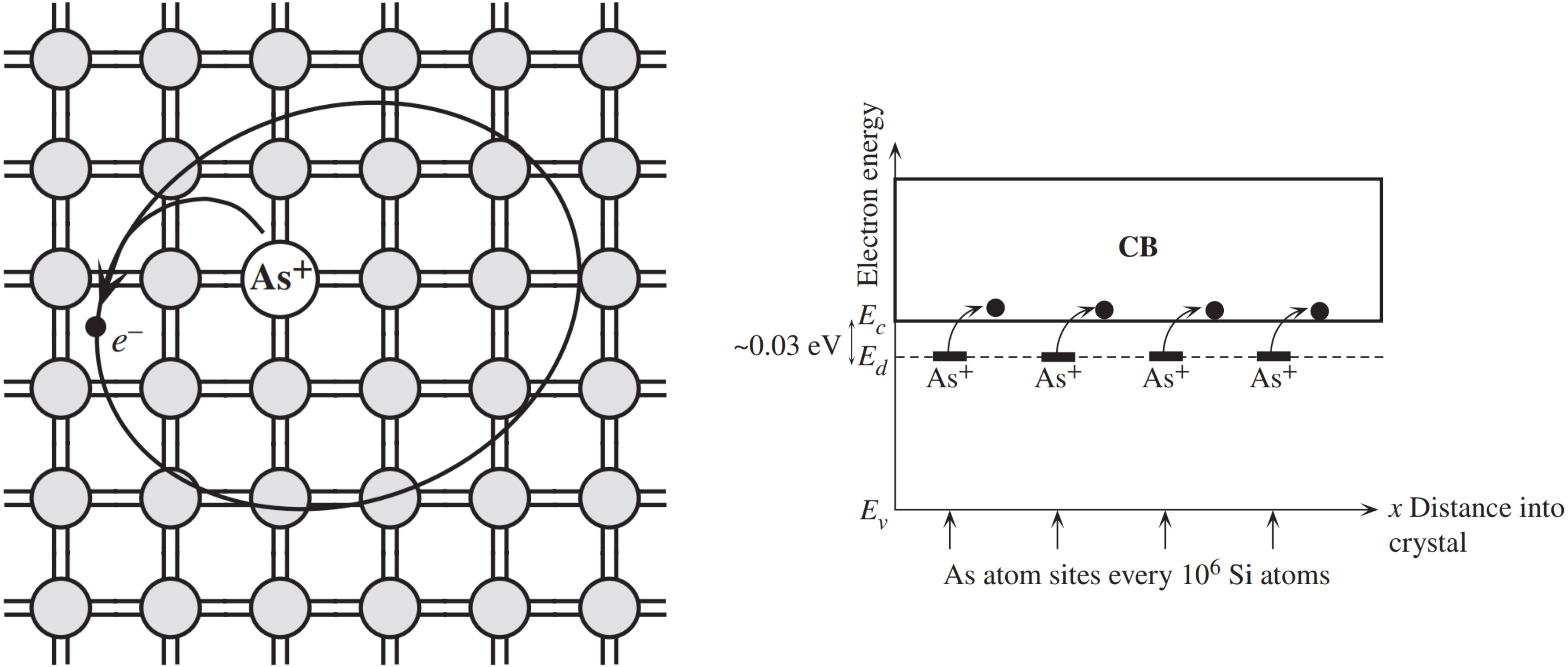
A two-dimensional pictorial view of the Si crystal showing covalent bonds as two lines where each line is a valence electron.

Arsenic-doped Si crystal



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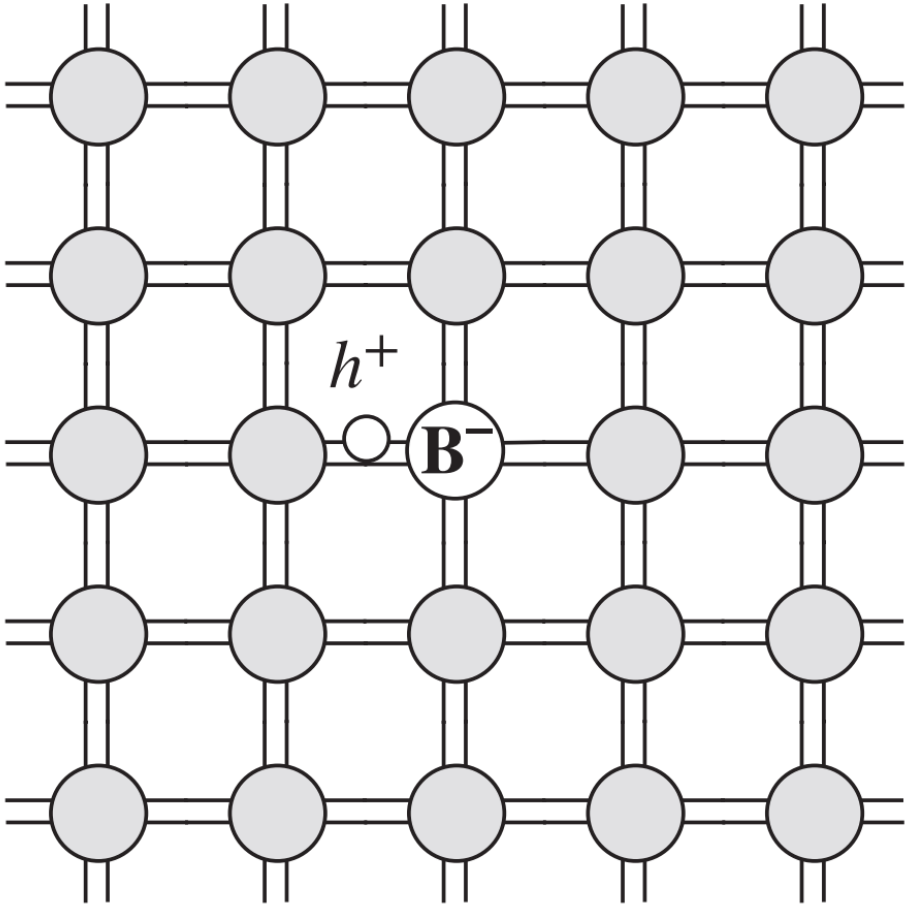
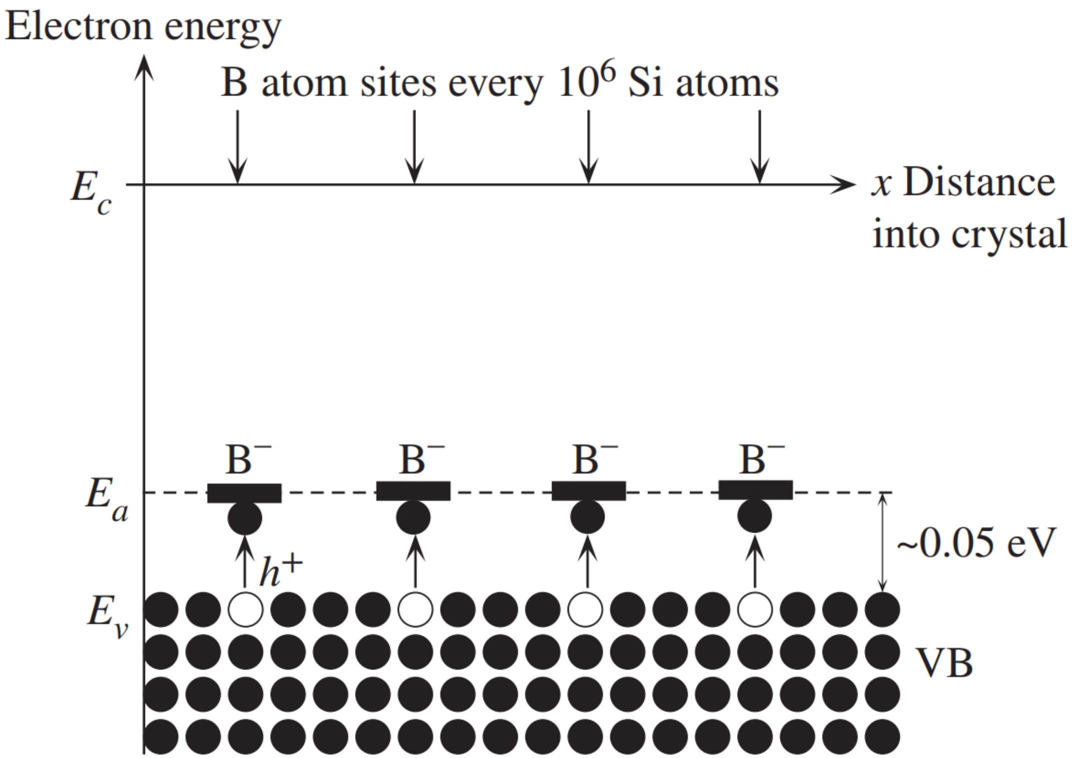
Boron-doped Si crystal





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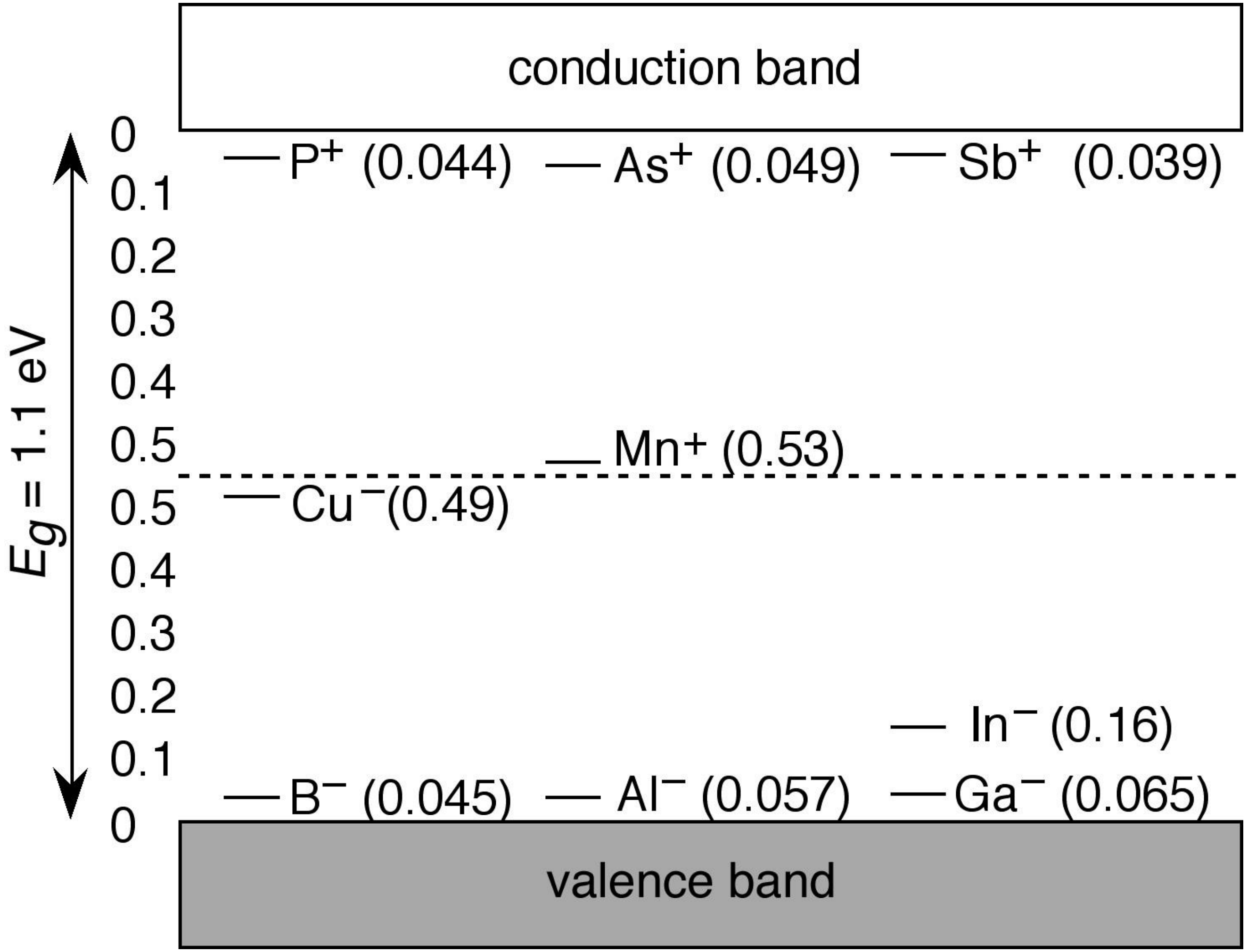
Strong and weak donors and acceptors



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The effective mass

The effective mass is a quantum mechanical quantity that behaves in the same way as the inertial mass in classical mechanics.

$$m_e^* = \frac{F_{\text{ext}}}{a_{\text{crystal}}}$$

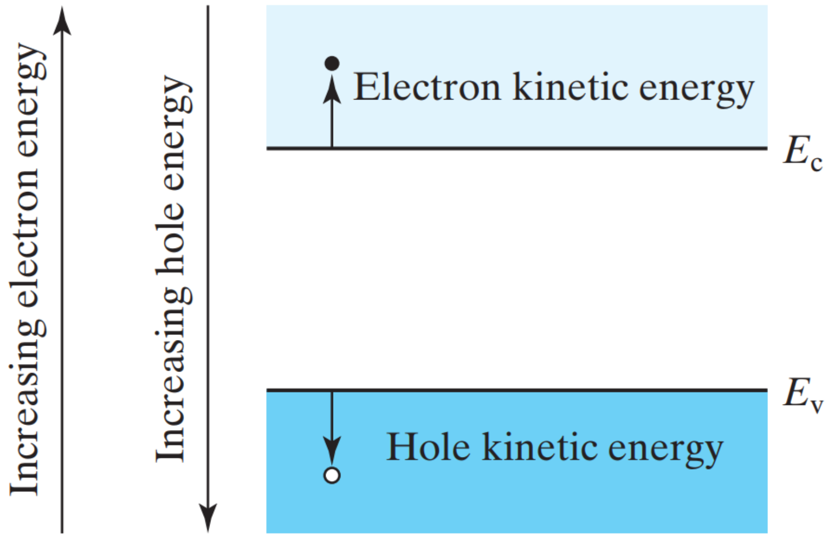
		Germanium	Silicon	GaAs
Smallest energy bandgap at 300 K	E_g (eV)	0.66	1.12	1.424
Electron effective mass for density of states calculations	$\frac{m^*_{e,dos}}{m_0}$	0.55	1.08	0.067
Hole effective mass for density of states calculations	$\frac{m^*_{h,dos}}{m_0}$	0.37	0.811	0.45
Electron effective mass for conductivity calculations	$\frac{m^*_{e,cond}}{m_0}$	0.12	0.26	0.067
Hole effective mass for conductivity calculations	$\frac{m^*_{h,cond}}{m_0}$	0.21	0.386	0.34

Semiconductor Devices – Zeghbroeck

The effective mass

	Si	Ge	GaAs	InAs	AlAs
m_n/m_0	0.26	0.12	0.068	0.023	2.0
m_p/m_0	0.39	0.30	0.50	0.30	0.3

Electron and hole effective masses, m_n and m_p , normalized to the free electron mass



Both electrons and holes tend to seek their lowest energy positions. Electrons tend to fall in the energy band diagram. Holes float up like bubbles in water.

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